COMPLIANT

HALOGEN

FREE



### Vishay Semiconductors

# Hyperfast Rectifier, 2 A FRED Pt®



### **LINKS TO ADDITIONAL RESOURCES**



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	2 A			
$V_R$	200 V			
V <sub>F</sub> at I <sub>F</sub>	0.75 V			
t <sub>rr</sub>	25 ns			
T <sub>J</sub> max.	175 °C			
Package	SMA (DO-214AC)			
Circuit configuration	Single			

#### **FEATURES**

- Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element.

### **MECHANICAL DATA**

Case: SMA (DO-214AC)

Molding compound meets UL 94 V-0 flammability rating

Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	$V_{RRM}$		200	V	
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>Sp</sub> = 138 °C	2	^	
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 6 ms square pulse	50	] ^	
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C	

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	200	-	-		
Forward voltage, per diode	$V_{F}$	I <sub>F</sub> = 2 A	-	0.88	0.95	V	
i olward voltage, per diode		I <sub>F</sub> = 2 A, T <sub>J</sub> = 125 °C	-	0.75	0.82		
Deverage leakers assument new diede	I <sub>R</sub>	$V_R = V_R$ rated	-	-	2		
Reverse leakage current, per diode		$T_J = 125 ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	1	8	μA	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	8	-	pF	



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 5$	$50 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	-	24	-	
Payaraa raaayan tima	t <sub>rr</sub>	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	25	
Reverse recovery time		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 2 A, dI <sub>F</sub> /dt = 200 A/μs, V <sub>R</sub> = 160 V	-	16	-	ns
		T <sub>J</sub> = 125 °C		-	22	-	
Dools woods on a surrount	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	2	-	- A
Peak recovery current		T <sub>J</sub> = 125 °C		-	3	-	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	16	-	
		T <sub>J</sub> = 125 °C		-	30	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C
Thermal resistance, junction to mount	$R_{thJM}$	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	11	21	°C/W
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Device mounted on PCB with recommended pad size	-	-	125	°C/W
Approximate weight				0.07		g
Approximate weight			0.002		oz.	
Marking device		Case style SMA (DO-214AC)		2	H2	

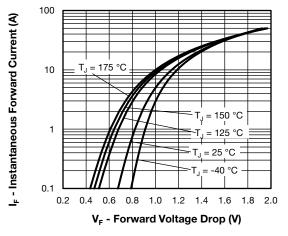


Fig. 1 - Typical Forward Voltage Drop Characteristics

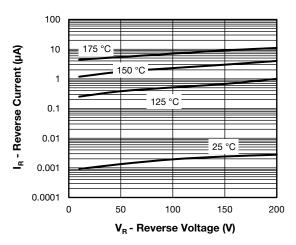


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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D = 0.02D = 0.05D = 0.1D = 0.2D = 0.5DC

2

2.5

3

3.5

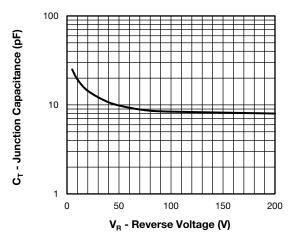
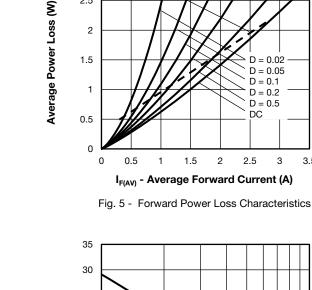


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage



3

2.5

2

**RMS** limit

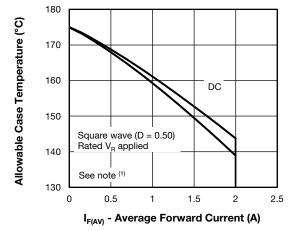


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

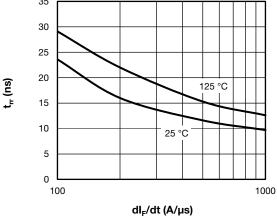


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

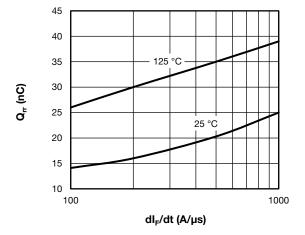
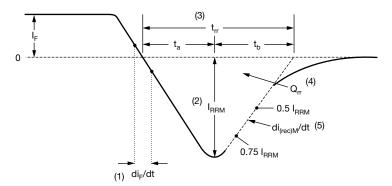


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $^{(1)}$  Formula used:  $T_{C} = T_{J}$  - (Pd + Pd\_{REV}) x  $R_{thJC};$ Pd = forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 5);  $Pd_{REV}$  = inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = rated  $V_R$ 

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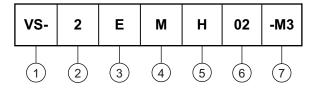
- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- and I<sub>RRM</sub>
- (2) I<sub>RRM</sub> peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RBM</sub> and 0.50 I<sub>RBM</sub> extrapolated to zero current.
- (5) di<sub>(rec)M</sub>/dt peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

(4) Q<sub>rr</sub> - area under curve defined by t<sub>rr</sub>

Fig. 8 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

### **Device code**



- Vishay Semiconductors product
- **2** Current rating (2 = 2 A)
- 3 Circuit configuration:

E = single diode

- 4 M = SMA package
- **5** Process type,

H = hyperfast recovery

- 6 Voltage code (02 = 200 V)
- 7 -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-2EMH02-M3/5AT	7500	7500	13"diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95400			
Part marking information	www.vishay.com/doc?95472			
Packaging information	www.vishay.com/doc?95404			
SPICE model	www.vishay.com/doc?96376			



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## **SMA**

### **DIMENSIONS** in inches (millimeters)

### **DO-214AC (SMA)**



### **Mounting Pad Layout**





### **Legal Disclaimer Notice**

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